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HMC441LH5* Product Page Quick Links

Last Content Update: 11/01/2016

Comparable Parts

View a parametric search of comparable parts

Evaluation Kits

- HMC441LH5 Evaluation Board

Documentation

Application Notes

- AN-1363: Meeting Biasing Requirements of Externally Biased RF/Microwave Amplifiers with Active Bias Controllers
- Broadband Biasing of Amplifiers General Application Note
- MMIC Amplifier Biasing Procedure Application Note
- Thermal Management for Surface Mount Components General Application Note

Data Sheet

- HMC441LH5 Data Sheet

Tools and Simulations

- HMC441LH5 S-Parameters

Reference Materials

Quality Documentation

- Semiconductor Qualification Test Report: PHEMT-F (QTR: 2013-00269)

Design Resources

- HMC441LH5 Material Declaration
- PCN-PDN Information
- Quality And Reliability
- Symbols and Footprints

Discussions

View all HMC441LH5 EngineerZone Discussions

Sample and Buy

Visit the product page to see pricing options

Technical Support

Submit a technical question or find your regional support number

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Typical Applications

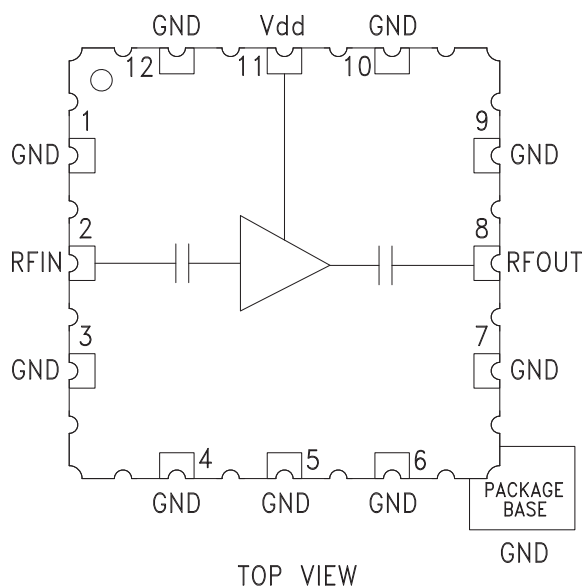
The HMC441LH5 is a medium PA for:

- Telecom Infrastructure
- Military Radio, Radar & ECM
- Space Systems
- Test Instrumentation

Features

- Gain: 5 dB
- Saturated Power: +21.5 dBm @ 25% PAE
- Single Positive Supply: +5V
- 50 Ohms Matched Input/Output
- Hermetic SMT Package, 25mm²
- Screening to MIL-PRF-38535 (Class B or S) Available

Functional Diagram



General Description

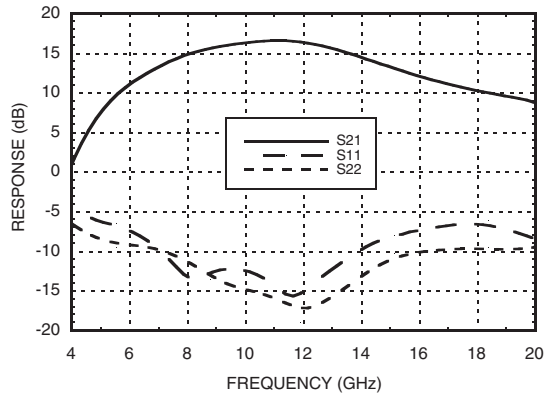
The HMC441LH5 is a broadband 7 to 15.5 GHz GaAs PHEMT MMIC Medium Power Amplifier housed in a hermetic SMT leadless package. The amplifier provides 15 dB of gain and 21.5 dBm of saturated power at 25% PAE from a +5V supply. This 50 Ohm matched amplifier does not require any external components, and the RF I/Os are DC blocked, making it an ideal linear gain block or driver amplifier. The HMC441LH5 allows the use of surface mount manufacturing techniques and is suitable for high reliability military, industrial & space applications.

Electrical Specifications, $T_A = +25^\circ\text{C}$, $V_{dd} = 5\text{V}$

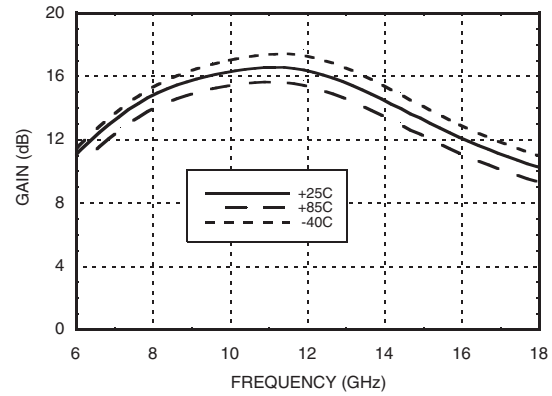
Parameter	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	Units
Frequency Range		7.0 - 8.0		8.0 - 13.0			13.0 - 14.0			14.0 - 15.5			GHz
Gain	11	14		13	16		12	15		10.5	13.5		dB
Gain Variation Over Temperature		0.015	0.02		0.015	0.02		0.015	0.02		0.015	0.02	dB/°C
Input Return Loss		11			13			10			8		dB
Output Return Loss		10			15			14			12		dB
Output Power for 1 dB Compression (P1dB)	15.5	18.5		17	20		16	19		16	19		dBm
Saturated Output Power (Psat)		20			21			21.5			21		dBm
Output Third Order Intercept (IP3)		30			32			32			32		dBm
Noise Figure		5.0			4.75			4.75			5.0		dB
Supply Current (Idd)		90	115		90	115		90	115		90	115	mA

GaAs PHEMT MMIC MEDIUM POWER AMPLIFIER, 7 - 15.5 GHz

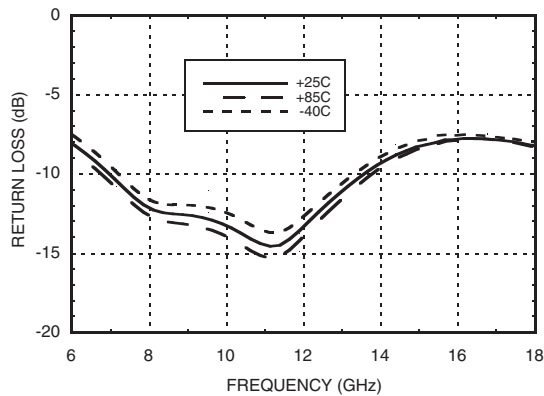
Broadband Gain & Return Loss



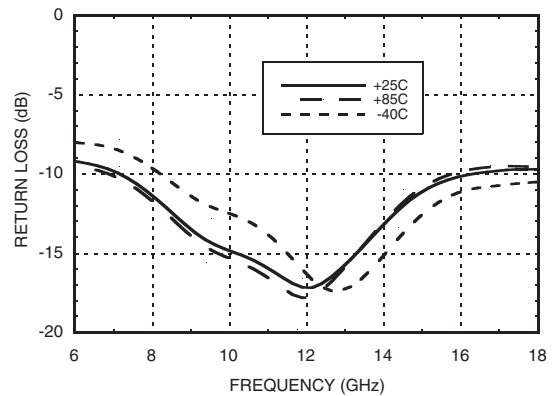
Gain vs. Temperature



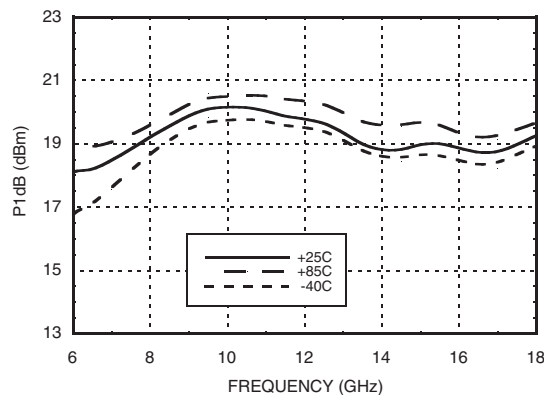
Input Return Loss vs. Temperature



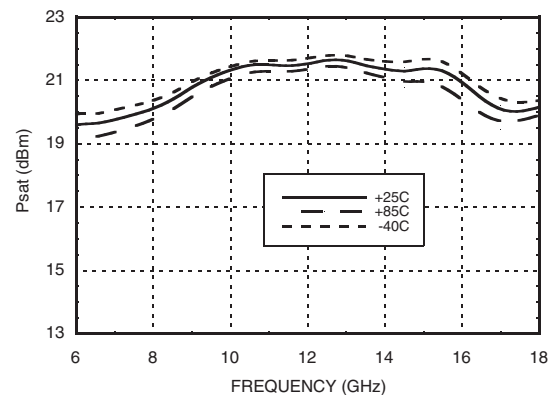
Output Return Loss vs. Temperature



P_{1dB} vs. Temperature

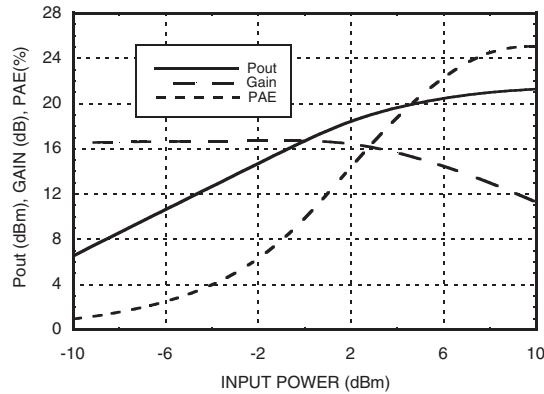


P_{sat} vs. Temperature

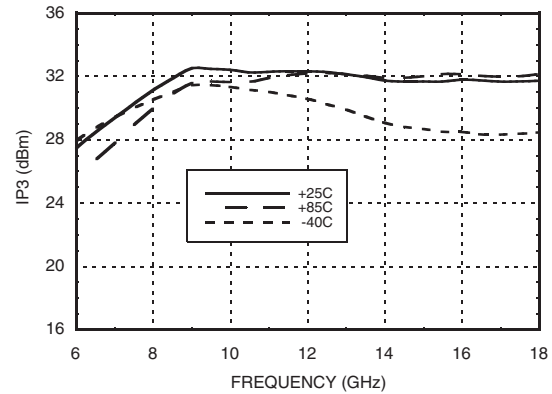


GaAs PHEMT MMIC MEDIUM POWER AMPLIFIER, 7 - 15.5 GHz

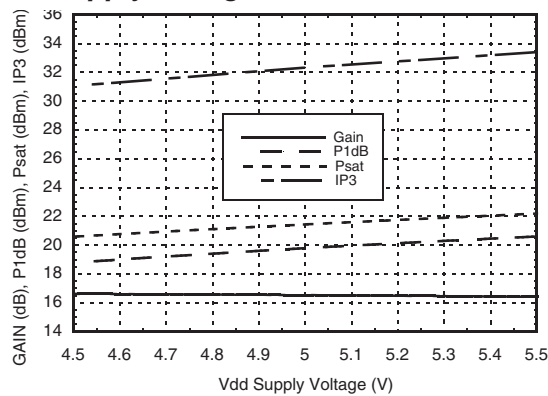
Power Compression @ 12 GHz



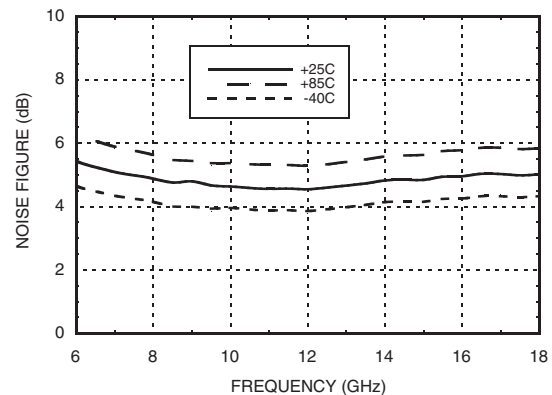
Output IP3 vs. Temperature



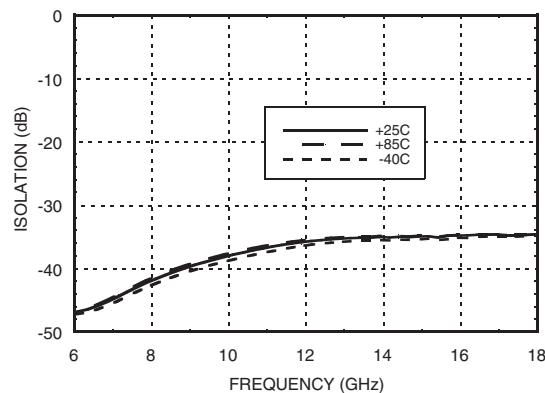
**Gain, Power & Output IP3
vs. Supply Voltage @ 12 GHz**



Noise Figure vs. Temperature



Reverse Isolation vs. Temperature



GaAs PHEMT MMIC MEDIUM POWER AMPLIFIER, 7 - 15.5 GHz

Absolute Maximum Ratings

Drain Bias Voltage (Vdd)	+6 Vdc
RF Input Power (RFIN)(Vdd = +5Vdc)	+15 dBm
Channel Temperature	175 °C
Continuous P _{diss} (T = 85 °C) (derate 8.4 mW/°C above 85 °C)	0.76 W
Thermal Resistance (channel to ground paddle)	118.8 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-40 to +85 °C

Typical Supply Current vs. Vdd

Vdd (V)	Idd (mA)
+5.5	92
+5.0	90
+4.5	88

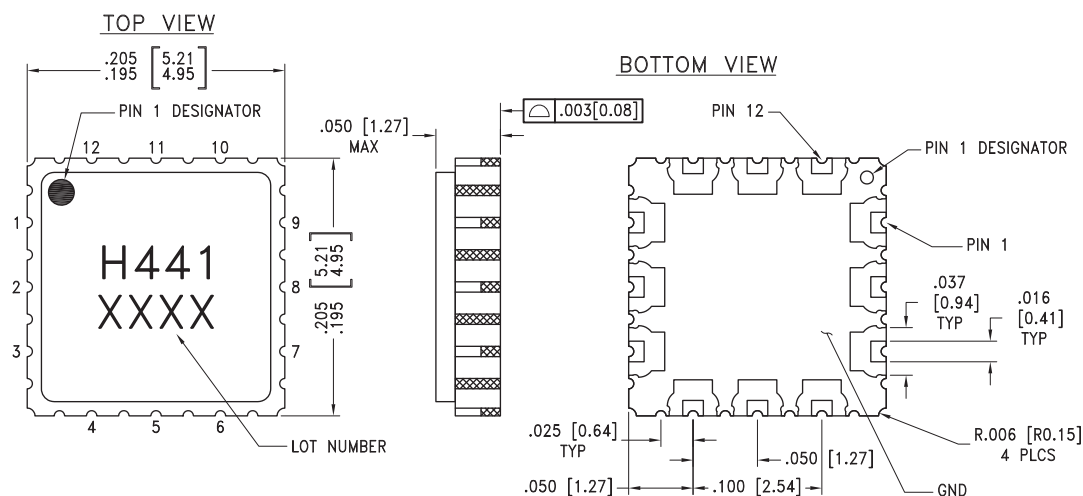
Note: Amplifier will operate over full voltage range shown above



ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS

11

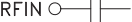
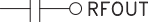
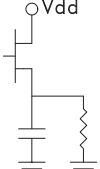
Outline Drawing



NOTES:

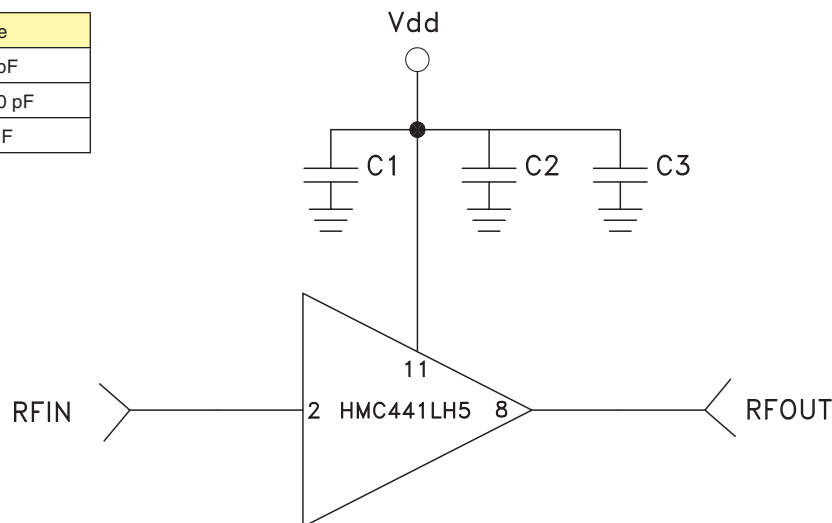
1. PACKAGE BODY MATERIAL: CERAMIC & KOVAR
2. LEAD AND GROUND PADDLE PLATING: GOLD 40 - 80 MICROINCHES.
3. DIMENSIONS ARE IN INCHES [MILLIMETERS].
4. LEAD SPACING TOLERANCE IS NON-CUMULATIVE
5. PAD BURR LENGTH 0.15mm MAX.
PAD BURR HEIGHT 0.25mm MAX.
6. ALL GROUND LEADS AND GROUND PADDLE MUST BE SOLDERED TO PCB RF GROUND.

Pin Descriptions

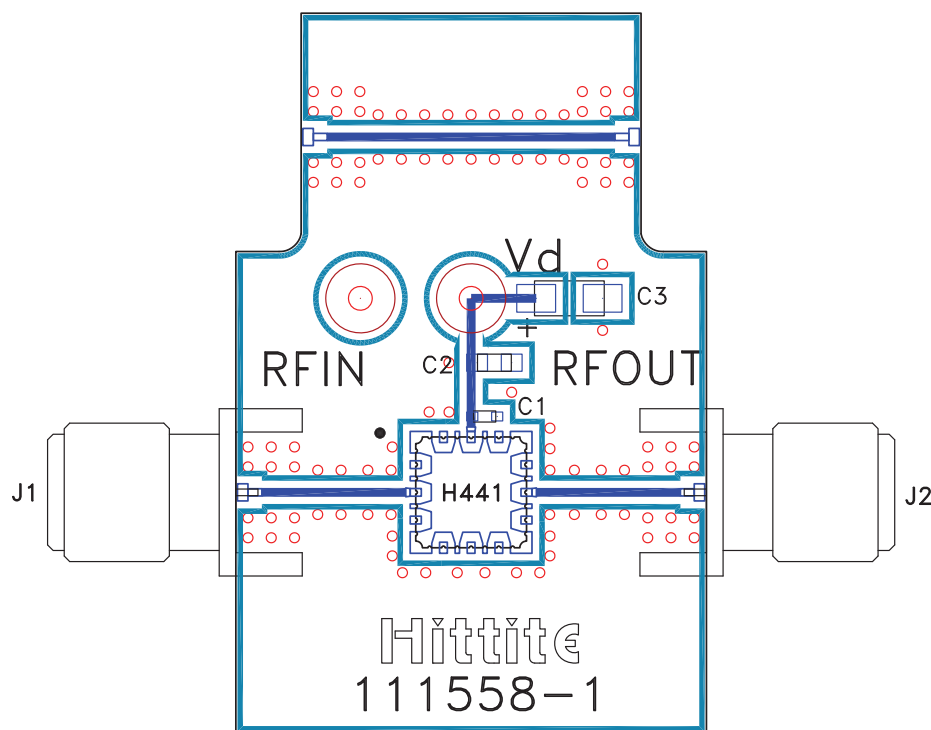
Pin Number	Function	Description	Interface Schematic
1, 3-7, 9, 10, 12	GND	These pins and package bottom must be connected to RF/DC ground.	
2	RFIN	This pin is AC coupled and matched to 50 Ohms.	
8	RFOUT	This pin is AC coupled and matched to 50 Ohms.	
11	Vdd	Power Supply Voltage for the amplifier. External bypass capacitors are recommended.	

Application Circuit

Component	Value
C1	100 pF
C2	1,000 pF
C3	4.7 μF



Evaluation PCB



List of Materials for Evaluation PCB 111560 [1]

Item	Description
J1 - J2	PCB Mount SMA RF Connector, SRI
U1	HMC441LH5
C1	100 pF Capacitor, 0402 Pkg.
C2	1,000 pF Capacitor, 0603 Pkg.
C3	4.7 μ F Capacitor, Tantalum
PCB [2]	111558 Evaluation Board

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350

The circuit board used in the final application should use RF circuit design techniques. Signal lines should have 50 ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation circuit board shown is available from Hittite upon request.